NSN 5961-01-083-7886

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-083-7886

Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

0.328 inches

Overall Width:

1.050 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact-darlington connected

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 collector to base voltage/static/emitter open and 100.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

Between 0.20 amperes source cutoff current and 12.00 amperes source cutoff current

Power Rating Per Characteristic:

150.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

1 case and 2 pin

Specification Data:

81349-mil-prf-19500/502 government specification

Shelf Life:

N/a

Unit Of Measure:

NSN 5961-01-083-7886

Transistor - Page 2 of 2

Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.

